

IGBT - Power, Co-PAK, N-Channel, Field Stop VII, (FS7), SCR, Power TO247-3L 1200 V, 1.4 V, 25 A FGHL25T120RWD

Description

Using the novel field stop 7th generation IGBT technology and the Gen7 Diode in TO247 3-lead package, this device offers the optimum performance with low on state voltage and minimal switching losses for both hard and soft switching topologies in industrial applications.

Features

- Extremely Efficient Trench with Field Stop Technology
- Maximum Junction Temperature – $T_J = 175^\circ\text{C}$
- Short Circuit Rated and Low Saturation Voltage
- Fast Switching and Tightened Parameter Distribution
- This Device is Pb-Free, Halogen Free/BFR Free and is RoHS Compliant

Applications

- Motor Drive
- UPS
- Energy Storage System
- General Inverter for Low Conduction Loss Applications

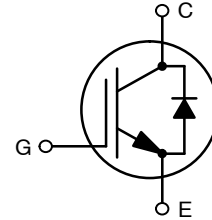
MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit	
Collector-to-Emitter Voltage	V_{CE}	1200	V	
Gate-to-Emitter Voltage	V_{GE}	± 20	V	
Transient Gate-to-Emitter Voltage		± 30		
Collector Current	I_C	$T_C = 25^\circ\text{C}$	50	A
		$T_C = 100^\circ\text{C}$	25	
Power Dissipation	P_D	$T_C = 25^\circ\text{C}$	468	W
		$T_C = 100^\circ\text{C}$	234	
Pulsed Collector Current	I_{CM}	$T_C = 25^\circ\text{C}$, $t_p = 10 \mu\text{s}$ (Note 1)	75	A
Diode Forward Current	I_F	$T_C = 25^\circ\text{C}$	50	A
		$T_C = 100^\circ\text{C}$	25	
Pulsed Diode Maximum Forward Current	I_{FM}	$T_C = 25^\circ\text{C}$, $t_p = 10 \mu\text{s}$ (Note 1)	75	A
Short Circuit Withstand Time $V_{GE} = 15 \text{ V}$, $V_{CC} = 800 \text{ V}$, $T_C = 150^\circ\text{C}$	T_{SC}	6	μs	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +175	$^\circ\text{C}$	
Lead Temperature for Soldering Purposes	T_L	260	$^\circ\text{C}$	

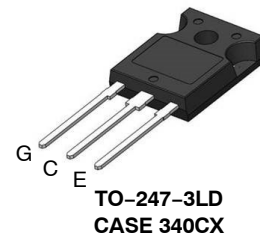
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: Pulse width limited by max. junction temperature

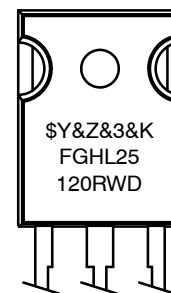
BV_{CES}	$V_{CE(sat)}$ TYP	I_C MAX
1200 V	1.4 V	25 A



COPACK IGBT



MARKING DIAGRAM



\$Y	= onsemi Logo
&Z	= Assembly Plant Code
&3	= 3-Digit Date Code
&K	= 2-Digit Lot Traceability Code
FGHL25120RWD	= Specific Device Code

ORDERING INFORMATION

Device	Package	Shipping
FGHL25T120RWD	TO247-3L (Pb-Free)	30 Units / Tube

FGHL25T120RWD

THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance Junction-to-Case, for IGBT	$R_{\theta JC}$	0.32	°C/W
Thermal Resistance Junction-to-Case, for Diode		0.59	
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	40	

ELECTRICAL CHARACTERISTICS OF IGBT

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Collector-to-Emitter Breakdown Voltage	BV_{CES}	$V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$	1200	-	-	V
Collector-to-Emitter Breakdown Voltage Temperature Coefficient	$\Delta BV_{CES} / \Delta T_J$	$V_{GE} = 0\text{ V}, I_C = 9.99\text{ mA}$	-	1226	-	mV/°C
Zero Gate Voltage Collector Current	I_{CES}	$V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$	-	-	40	μA
Gate-to-Emitter leakage Current	I_{GES}	$V_{GE} = \pm 20\text{ V}, V_{CE} = 0\text{ V}$	-	-	±400	nA

ON CHARACTERISTICS

Gate Threshold Voltage	$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 25\text{ mA}, T_J = 25^\circ\text{C}$	5.1	6.0	6.9	V
Gate-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE} = 15\text{ V}, I_C = 25\text{ A}, T_J = 25^\circ\text{C}$	-	1.40	1.73	V
		$V_{GE} = 15\text{ V}, I_C = 25\text{ A}, T_J = 175^\circ\text{C}$	-	1.62	-	

DYNAMIC CHARACTERISTICS

Input Capacitance	C_{IES}	$V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	-	3054	-	pF
Output Capacitance	C_{OES}		-	126	-	
Reverse Transfer Capacitance	C_{RES}		-	15.4	-	
Total Gate Charge	Q_G	$V_{CE} = 600\text{ V}, I_C = 25\text{ A}, V_{GE} = 15\text{ V}$	-	113	-	nC
Gate-to-Emitter Charge	Q_{GE}		-	27.2	-	
Gate-to-Collector Charge	Q_{GC}		-	49.5	-	

SWITCHING CHARACTERISTIC, INDUCTIVE LOAD

Turn-On Delay Time	$t_{d(on)}$	$V_{CE} = 600\text{ V}, V_{GE} = 0/15\text{ V}, I_C = 12.5\text{ A}, R_G = 4.7\ \Omega, T_J = 25^\circ\text{C}$	-	33.8	-	ns	
Turn-Off Delay Time	$t_{d(off)}$		-	223	-		
Rise Time	t_r		-	19.7	-		
Fall Time	t_f		-	192	-		
Turn-On Switching Loss	E_{on}		$V_{CE} = 600\text{ V}, V_{GE} = 0/15\text{ V}, I_C = 25\text{ A}, R_G = 4.7\ \Omega, T_J = 25^\circ\text{C}$	-	0.55	-	mJ
Turn-Off Switching Loss	E_{off}			-	0.86	-	
Total Switching Loss	E_{ts}			-	1.41	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{CE} = 600\text{ V}, V_{GE} = 0/15\text{ V}, I_C = 25\text{ A}, R_G = 4.7\ \Omega, T_J = 25^\circ\text{C}$		-	36.9	-	ns
Turn-Off Delay Time	$t_{d(off)}$			-	175	-	
Rise time	t_r			-	35.4	-	
Fall Time	t_f			-	126	-	
Turn-On Switching Loss	E_{on}		$V_{CE} = 600\text{ V}, V_{GE} = 0/15\text{ V}, I_C = 25\text{ A}, R_G = 4.7\ \Omega, T_J = 25^\circ\text{C}$	-	1.57	-	mJ
Turn-Off Switching Loss	E_{off}			-	1.06	-	
Total Switching Loss	E_{ts}			-	2.62	-	

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ELECTRICAL CHARACTERISTICS OF IGBT (continued)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
SWITCHING CHARACTERISTIC, INDUCTIVE LOAD						
Turn-On Delay Time	$t_{d(on)}$	$V_{CE} = 600\text{ V}, V_{GE} = 0/15\text{ V},$ $I_C = 12.5\text{ A}, R_G = 4.7\ \Omega,$ $T_J = 175^\circ\text{C}$	-	37.7	-	ns
Turn-Off Delay Time	$t_{d(off)}$		-	315	-	
Rise Time	t_r		-	27.1	-	
Fall Time	t_f		-	384	-	
Turn-On Switching Loss	E_{on}		-	0.78	-	mJ
Turn-Off Switching Loss	E_{off}		-	1.6	-	
Total Switching Loss	E_{ts}		-	2.38	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{CE} = 600\text{ V}, V_{GE} = 0/15\text{ V},$ $I_C = 25\text{ A}, R_G = 4.7\ \Omega, T_J = 175^\circ\text{C}$	-	42.2	-	ns
Turn-Off Delay Time	$t_{d(off)}$		-	235	-	
Rise Time	t_r		-	46.5	-	
Fall Time	t_f		-	242	-	
Turn-On Switching Loss	E_{on}		-	2.23	-	mJ
Turn-Off Switching Loss	E_{off}		-	1.9	-	
Total Switching Loss	E_{ts}		-	4.14	-	

DIODE CHARACTERISTICS

Diode Forward Voltage	V_F	$I_F = 25\text{ A}, T_J = 25^\circ\text{C}$	-	1.7	2.0	V
		$I_F = 25\text{ A}, T_J = 175^\circ\text{C}$	-	1.67	-	

DIODE SWITCHING CHARACTERISTIC, INDUCTIVE LOAD

Reverse Recovery Time	t_{rr}	$V_R = 600\text{ V}, I_F = 12.5\text{ A},$ $di_F/dt = 500\text{ A}/\mu\text{s}, T_J = 25^\circ\text{C}$	-	133	-	ns
Reverse Recovery Charge	Q_{rr}		-	1179	-	nC
Reverse Recovery Energy	E_{rec}		-	0.39	-	mJ
Peak Reverse Recovery Current	I_{RRM}		-	22.1	-	A
Reverse Recovery Time	t_{rr}	$V_R = 600\text{ V}, I_F = 25\text{ A},$ $di_F/dt = 500\text{ A}/\mu\text{s}, T_J = 25^\circ\text{C}$	-	173	-	ns
Reverse Recovery Charge	Q_{rr}		-	2136	-	nC
Reverse Recovery Energy	E_{rec}		-	0.65	-	mJ
Peak Reverse Recovery Current	I_{RRM}		-	28.4	-	A
Reverse Recovery Time	t_{rr}	$V_R = 600\text{ V}, I_F = 12.5\text{ A},$ $di_F/dt = 500\text{ A}/\mu\text{s}, T_J = 175^\circ\text{C}$	-	180	-	ns
Reverse Recovery Charge	Q_{rr}		-	1775	-	nC
Reverse Recovery Energy	E_{rec}		-	0.67	-	mJ
Peak Reverse Recovery Current	I_{RRM}		-	24.5	-	A
Reverse Recovery Time	t_{rr}	$V_R = 600\text{ V}, I_F = 25\text{ A},$ $di_F/dt = 500\text{ A}/\mu\text{s}, T_J = 175^\circ\text{C}$	-	229	-	ns
Reverse Recovery Charge	Q_{rr}		-	3383	-	nC
Reverse Recovery Energy	E_{rec}		-	1.16	-	mJ
Peak Reverse Recovery Current	I_{RRM}		-	34	-	A

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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TYPICAL CHARACTERISTICS

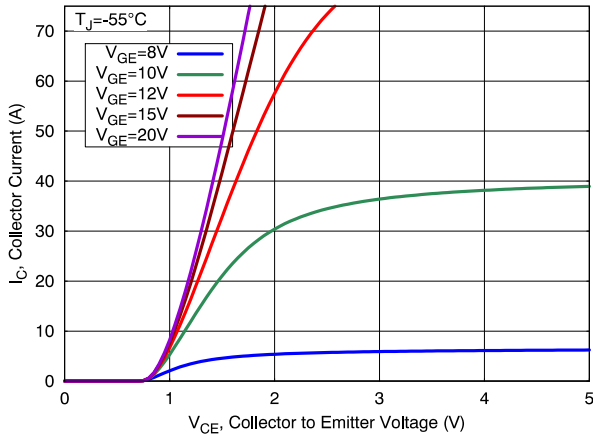


Figure 1. Output Characteristics

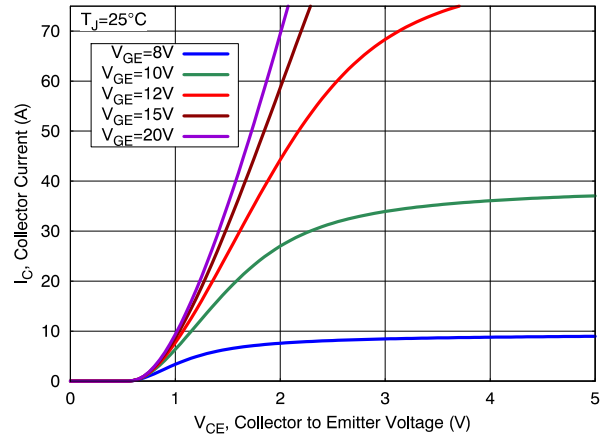


Figure 2. Output Characteristics

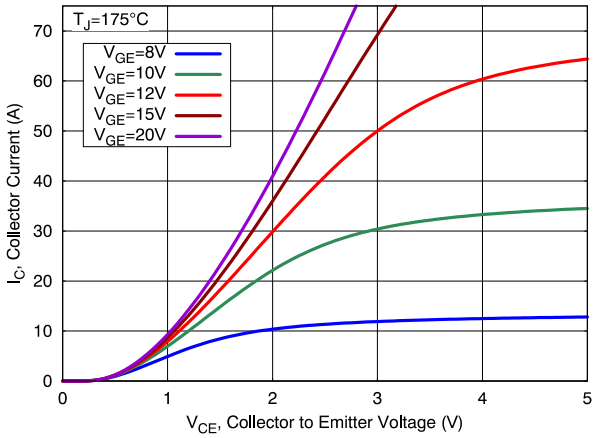


Figure 3. Output Characteristics

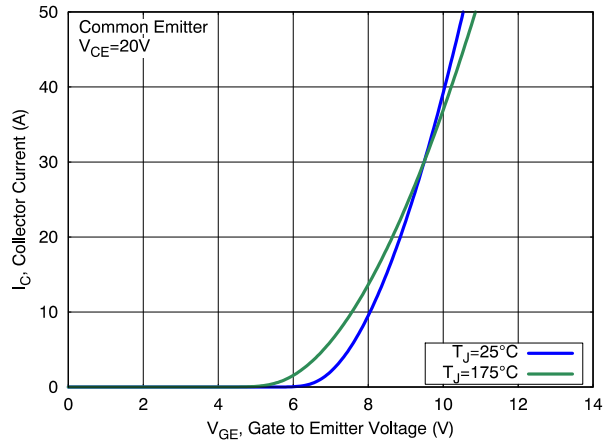


Figure 4. Transfer Characteristics

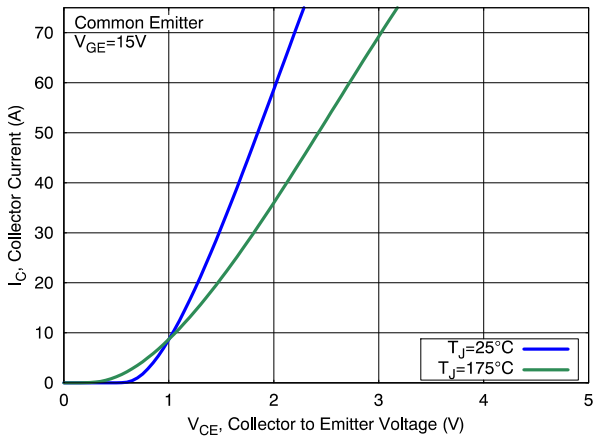


Figure 5. Saturation Characteristics

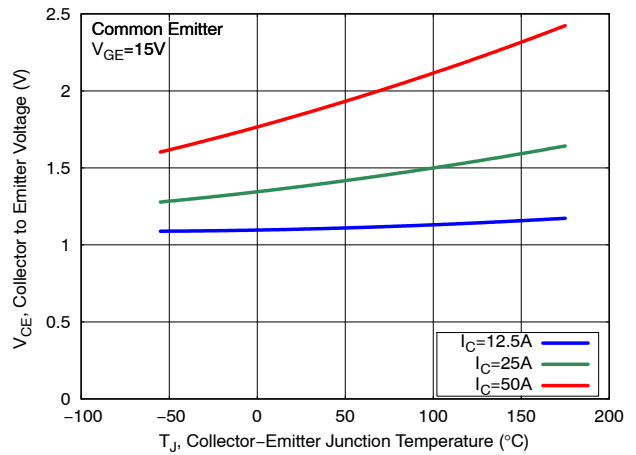


Figure 6. Saturation Voltage vs. Junction Temperature

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TYPICAL CHARACTERISTICS

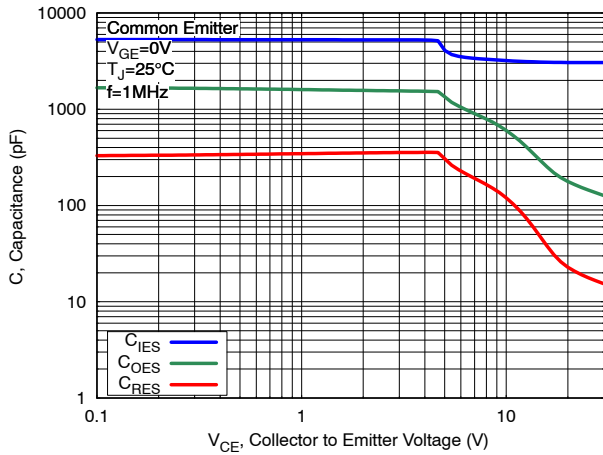


Figure 7. Capacitance Characteristics

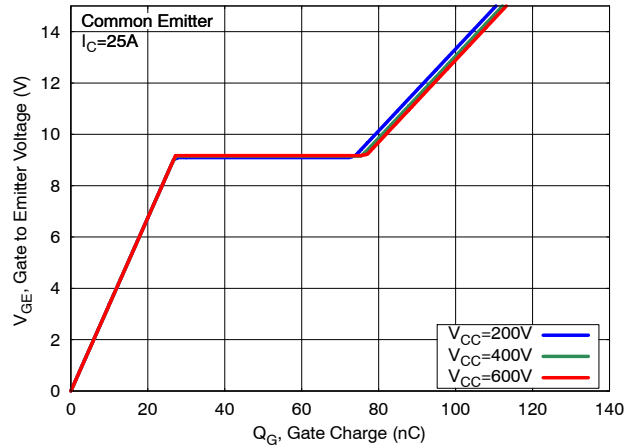


Figure 8. Gate Charge Characteristics

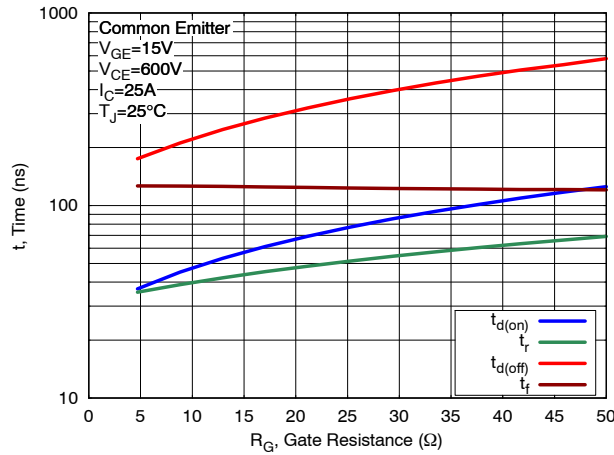


Figure 9. Switching Time vs Gate Resistance

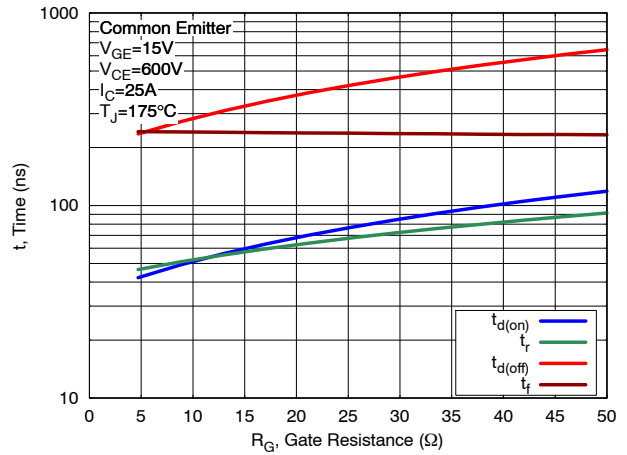


Figure 10. Switching Time vs Gate Resistance

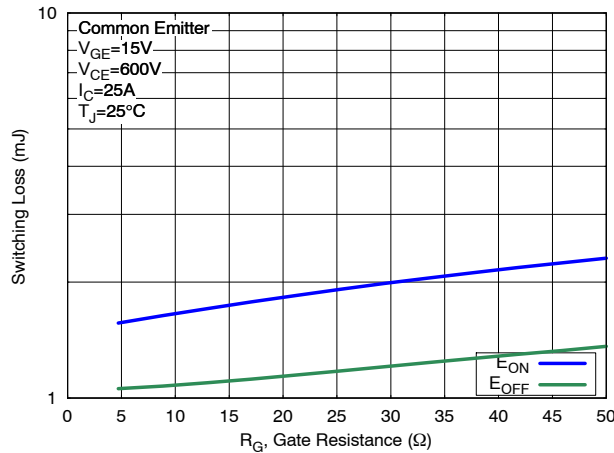


Figure 11. Switching Loss vs Gate Resistance

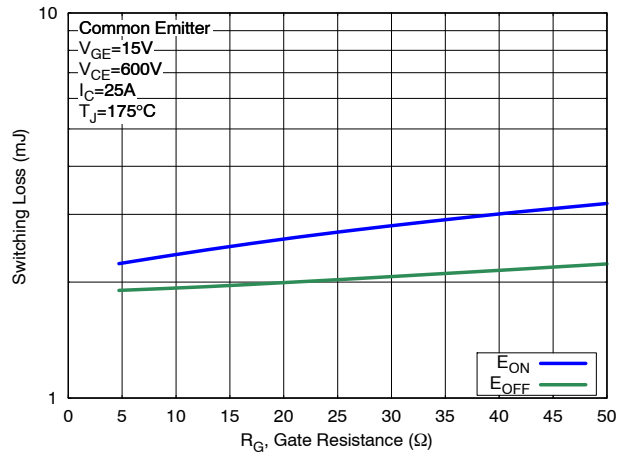


Figure 12. Switching Loss vs Gate Resistance

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TYPICAL CHARACTERISTICS

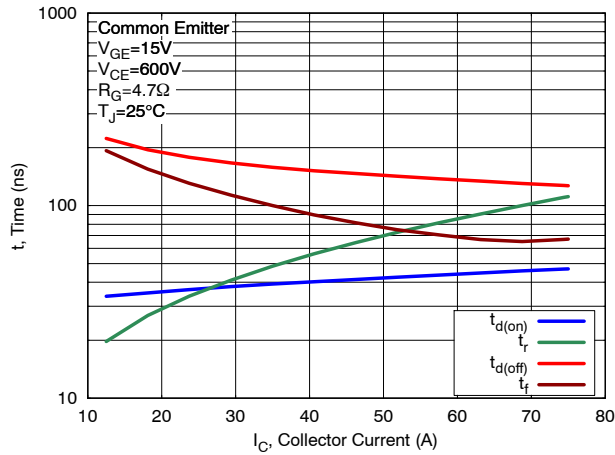


Figure 13. Switching Time vs Collector Current

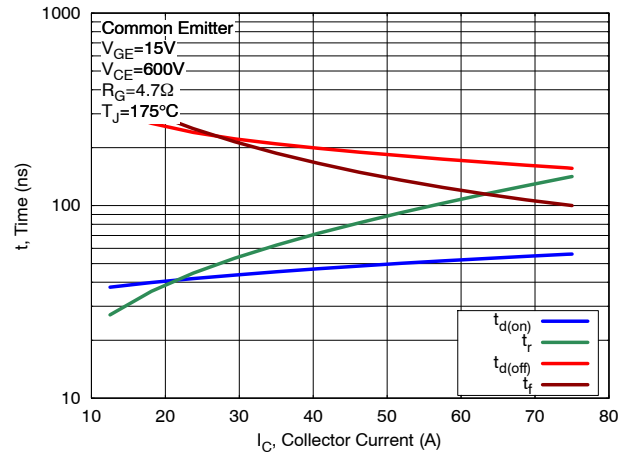


Figure 14. Switching Time vs Collector Current

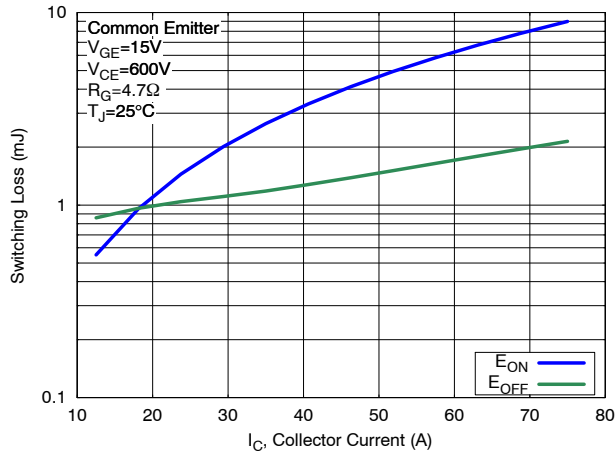


Figure 15. Switching Loss vs Collector Current

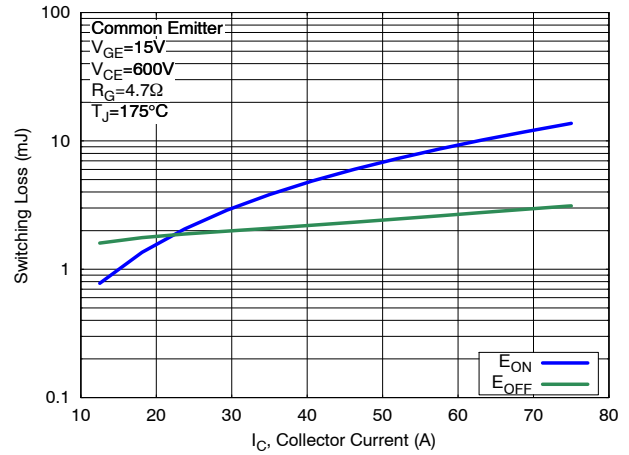


Figure 16. Switching Loss vs Collector Current

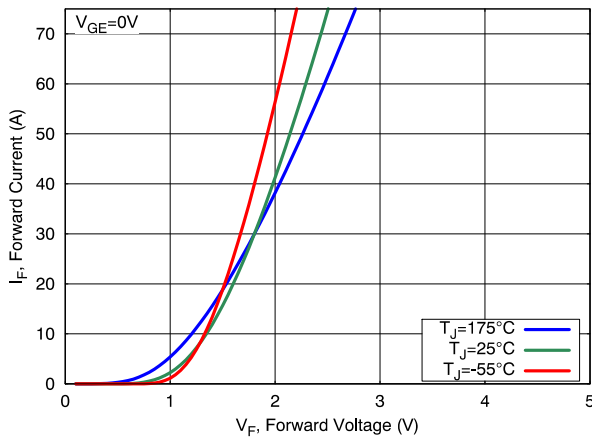


Figure 17. Diode Forward Characteristics

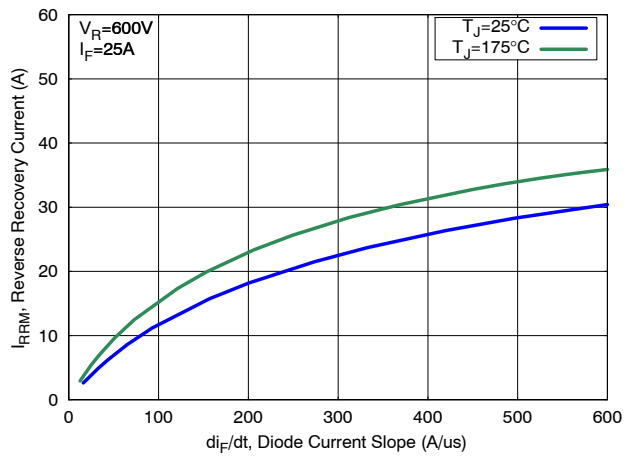


Figure 18. Diode Reverse Recovery Current

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TYPICAL CHARACTERISTICS

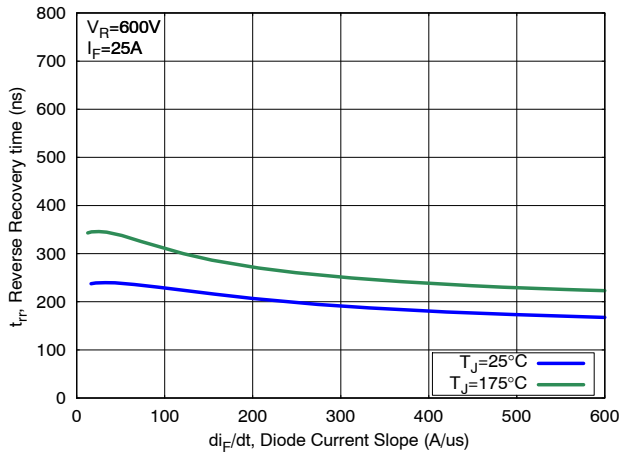


Figure 19. Diode Reverse Recovery Current

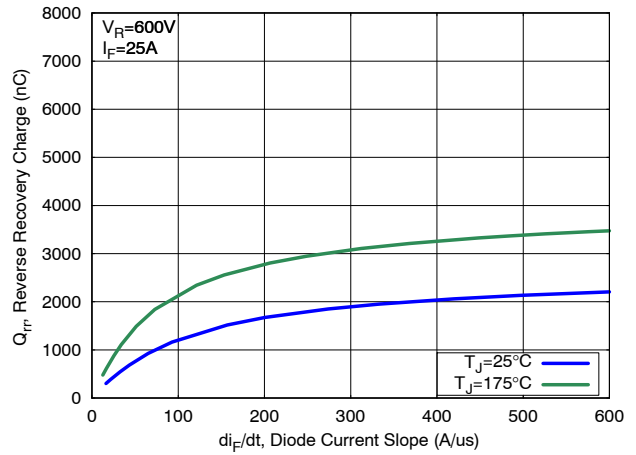


Figure 20. Diode Stored Charge Characteristics

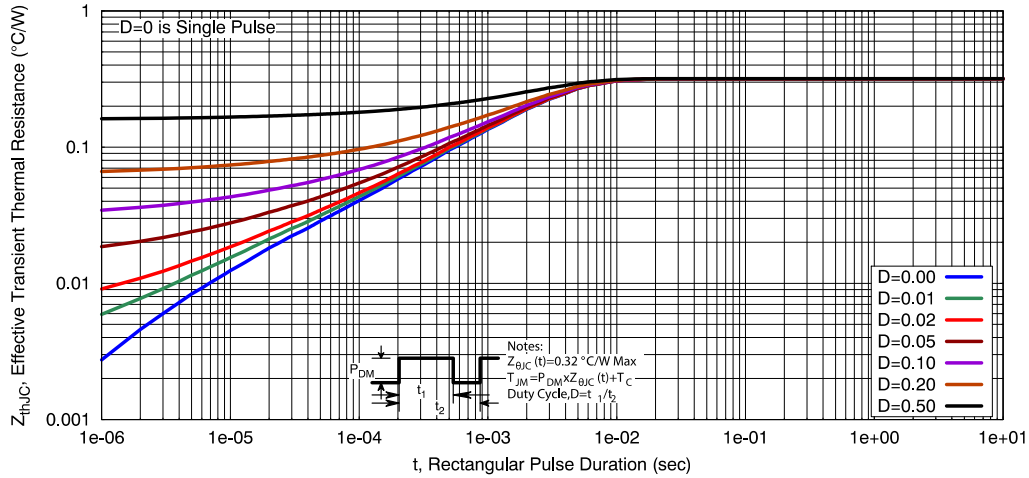


Figure 21. Transient Thermal Impedance of IGBT

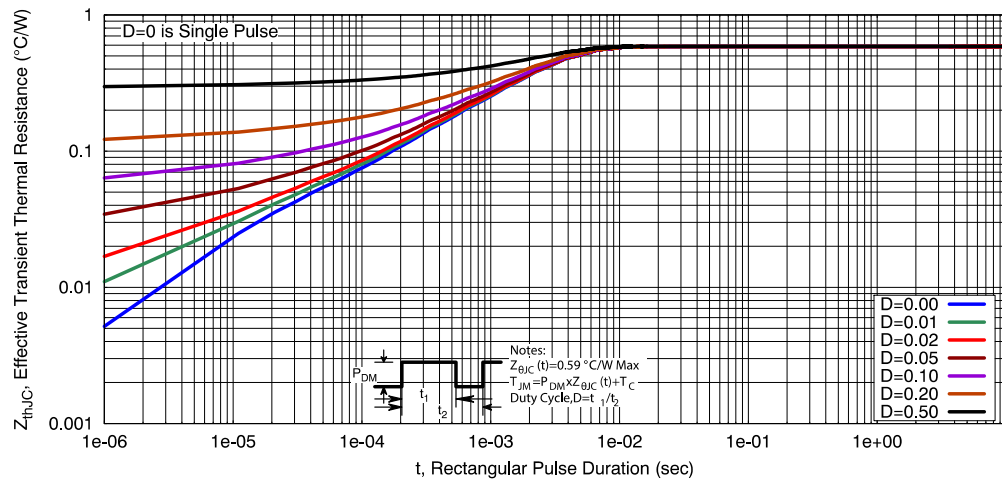


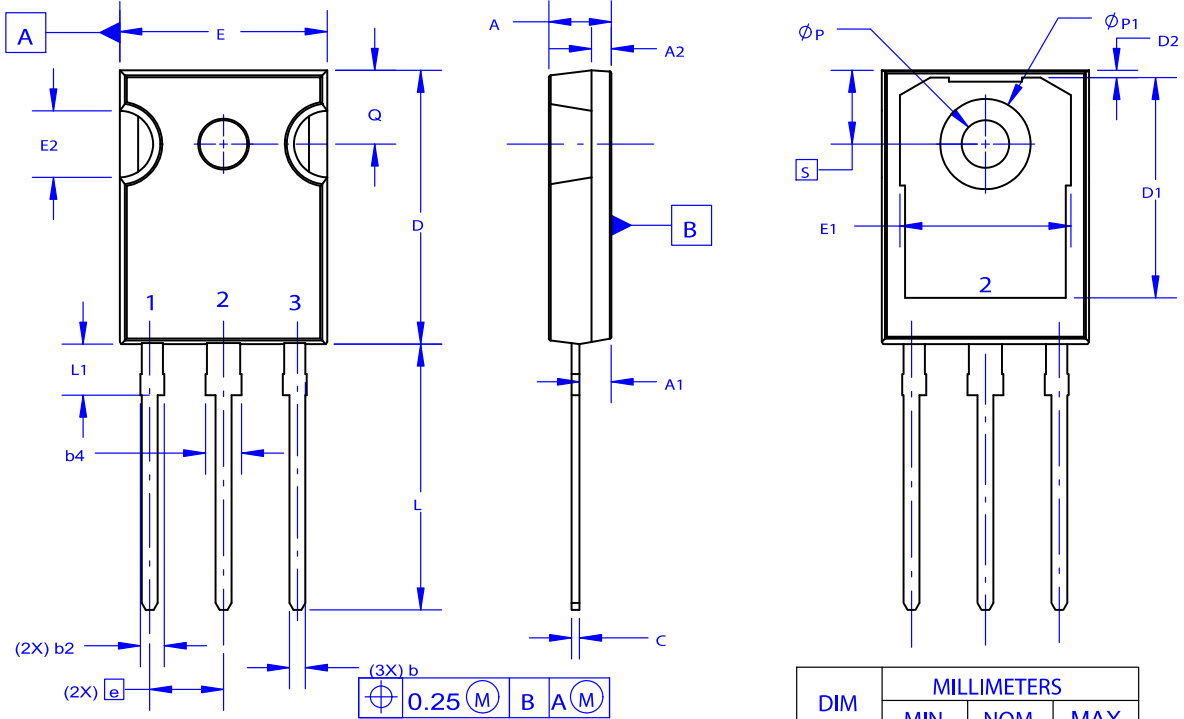
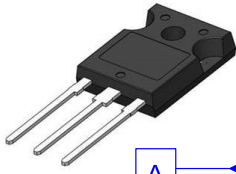
Figure 22. Transient Thermal Impedance of Diode

FGHL25T120RWD

PACKAGE DIMENSIONS

TO-247-3LD
CASE 340CX
ISSUE A

DATE 06 JUL 2020



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
- D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.20	2.40	2.60
A2	1.40	1.50	1.60
D	20.32	20.57	20.82
E	15.37	15.62	15.87
E2	4.96	5.08	5.20
e	~	5.56	~
L	19.75	20.00	20.25
L1	3.69	3.81	3.93
∅P	3.51	3.58	3.65
Q	5.34	5.46	5.58
S	5.34	5.46	5.58
b	1.17	1.26	1.35
b2	1.53	1.65	1.77
b4	2.42	2.54	2.66
c	0.51	0.61	0.71
D1	13.08	~	~
D2	0.51	0.93	1.35
E1	12.81	~	~
∅P1	6.60	6.80	7.00

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